Supplementary Material

Flexible Metal Oxide Thin-Film Transistors Produced by Nanofiber-to-Film Process

Danna Zhang[a,b,1], *Guangtan Miao*[a,b,1], *Guoxia Liu*[a,b,2], *and Fukai Shan*[a,b,2]

[a]College of Physics, Qingdao University, Qingdao 266071, China

[b]College of Microtechnology & Nanotechnology, Qingdao University, Qingdao 266071, China

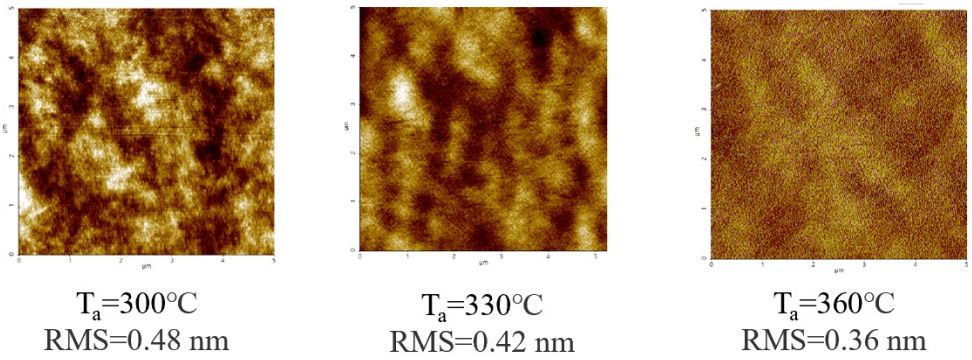

Fig. S1 AFM images of In_2O_3 thin-films annealed at various temperatures.

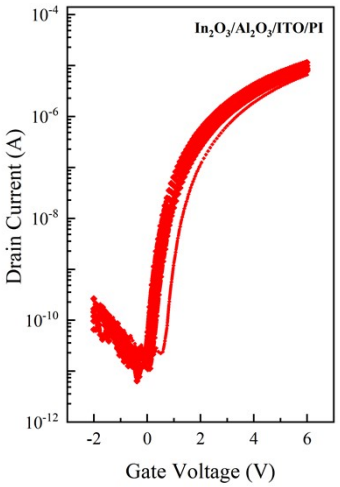

Fig. S2 Transfer curves of flexible In_2O_3/Al_2O_3 TFT array (4×5).

[1] Danna Zhang and Guangtan Miao contributed equally to this work.

[2] Corresponding author: Guoxia Liu (gxliu@qdu.edu.cn), Fukai Shan (fkshan@qdu.edu.cn)

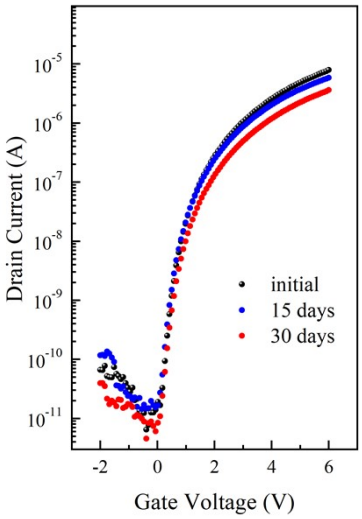

Fig. S3 Transfer curves of flexible In_2O_3/Al_2O_3 TFT after 30 days with aging.

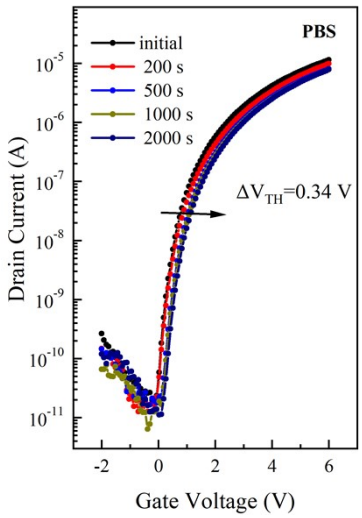

Fig. S4 PBS tests (V_{GS} = 3 V) for flexible In_2O_3/Al_2O_3 TFTs.